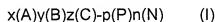


## IN THE CLAIMS

The following is a listing of the claims in the application, with claims 1 and 5 shown as amended and claims 6 and 7 cancelled.

### LISTING OF CLAIMS

1. (Currently Amended) A method for preparing a film structure of a ferroelectric single crystal, which comprises adhering a ferroelectric single crystal plate to a substrate by a conductive adhesive ~~or metal layer~~, wherein the ferroelectric single crystal is a material having the composition of formula (I):



wherein

is  $Pb(Mg_{1/3}Nb_{2/3})O_3$  or  $Pb(Zn_{1/3}Nb_{2/3})O_3$ ,

is  $PbTiO_3$ ,

is  $LiTaO_3$ ,

(P) is a metal selected from the group consisting of Pt, Au, Ag, Pd and Rh,

(N) is an oxide of a metal selected from the group consisting of Ni, Co, Fe, Sr, Sc, Ru, Cu and Cd,

x is a number in the range of 0.65 to 0.98,

y is a number in the range of 0.01 to 0.34,

z is a number in the range of 0.01 to 0.1, and

p and n are each independently a number in the range of 0.01 to 5,

wherein the conductive adhesive is a gold- or silver- containing epoxy paste, or a Pt-containing adhesive sol.

2. (Previously Amended) The method of claim 1, wherein the single crystal plate is polished to a thickness of 1 to 100  $\mu\text{m}$  before or after the adhesion with the substrate.

3. (Original) The method of claim 1, wherein the single crystal plate is adhered to the substrate by placing a conductive adhesive between the single crystal plate and the substrate and heat treating the resulting laminate containing the adhesive at a temperature ranging from room temperature to 150 °C for 1 to 24 hours to cure the adhesive.

4. (cancelled)

5. (currently amended) The method of claim [3] 1, wherein the adhesive is applied using terminal portion made of an elastic rubber.

6. (cancelled)

7. (cancelled)

8. (Original) The method of claim 1, wherein the ferroelectric single crystal has a dielectric constant of 1,000 or greater as measured in a film form.

9. (Cancelled)

10. (Original) The method of claim 1, wherein the substrate comprises a layer of an oxide material selected from SiO<sub>2</sub>, MgO, Al<sub>2</sub>O<sub>3</sub> and ZnO, the oxide layer being  
co  
ntacted with the conductive adhesive layer.

11. (Original) The method of claim 1, which further comprises forming a conductive metal layer on the surface of the single crystal plate opposite to the adhesive layer by a sputtering or an electronic beam evaporation method.

12. (Previously Amended) A ferroelectric single crystal film structure prepared by a method according to claim 1.

13. (Original) An electric or electronic device comprising the ferroelectric single crystal film structure according to claim 12.